Inventor(s): Ren-Guey Hsieh Serial No.: To Be Assigned

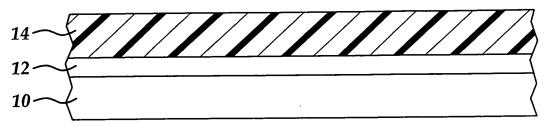
Filed: Herewith

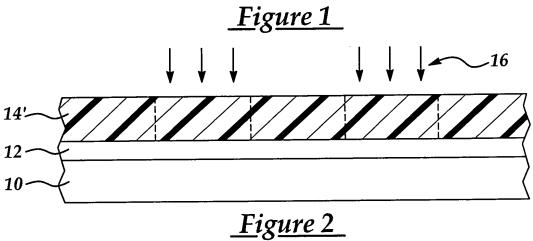
For: Gap Forming Pattern Fracturing Method ... Masking Layer

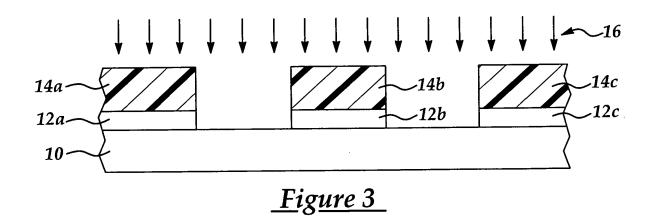
Attorney Docket No.: 67,200-447

BEST AVAILABLE COT.

1/2







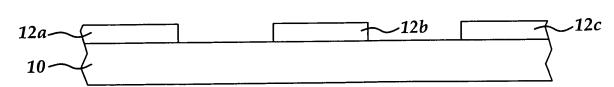


Figure 4

Filed: Herewith

For: Gap Forming Pattern Fracturing Method ... Masking Layer

Attorney Docket No.: 67,200-447

